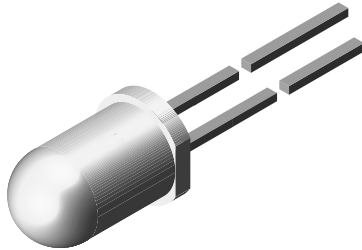


Infrared Emitting Diode, 875 nm, GaAlAs



94 8389

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Peak wavelength: $\lambda_p = 875$ nm
- High reliability
- Angle of half intensity: $\varphi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE

DESCRIPTION

The TSHA620. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

APPLICATIONS

- Infrared remote control and free air data transmission systems
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorption of 875 nm radiation in glass

PRODUCT SUMMARY				
COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSHA6200	40	± 12	875	600
TSHA6201	50	± 12	875	600
TSHA6202	60	± 12	875	600
TSHA6203	65	± 12	875	600

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA6200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6201	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6202	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6203	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	2.5	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	$^\circ C$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ C$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25 \text{ }^\circ C$, unless otherwise specified

TSHA6200, TSHA6201, TSHA6202, TSHA6203



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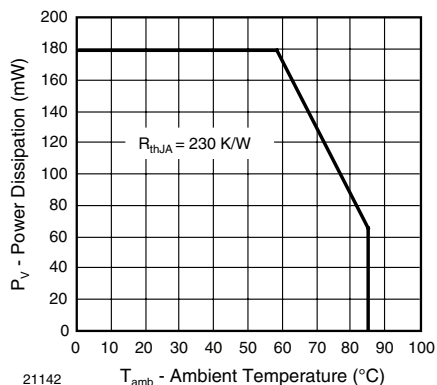


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

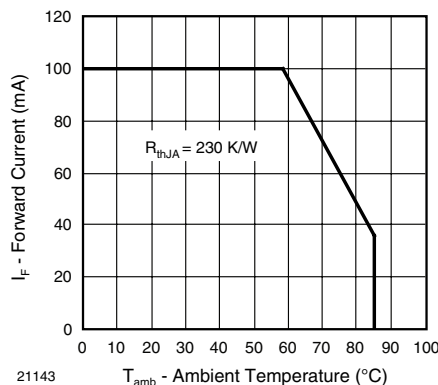


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.5	1.8	V
Temperature coefficient of V _F	I _F = 100 mA	TK _{V_F}		- 1.6		mV/K
Reverse current	V _R = 5 V	I _R			100	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		20		pF
Temperature coefficient of φ _e	I _F = 20 mA	TKφ _e		- 0.7		%/K
Angle of half intensity		φ		± 12		deg
Peak wavelength	I _F = 100 mA	λ _p		875		nm
Spectral bandwidth	I _F = 100 mA	Δλ		80		nm
Temperature coefficient of λ _p	I _F = 100 mA	TKλ _p		0.2		nm/K
Rise time	I _F = 100 mA	t _r		600		ns
	I _F = 1 A	t _r		300		ns
Fall time	I _F = 100 mA	t _f		600		ns
	I _F = 1 A	t _f		300		ns
Virtual source diameter		d		3.7		mm

Note

T_{amb} = 25 °C, unless otherwise specified



TSHA6200, TSHA6201, TSHA6202, TSHA6203

Infrared Emitting Diode, 875 nm, GaAlAs Vishay Semiconductors

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	TSHA6200	V_F		2.8	3.5	V
		TSHA6201	V_F		2.8	3.5	V
		TSHA6202	V_F		2.8	3.5	V
		TSHA6203	V_F		2.8	3.5	V
Radiant intensity	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSHA6200	I_e	25	40	125	mW/sr
		TSHA6201	I_e	30	50	125	mW/sr
		TSHA6202	I_e	36	60	125	mW/sr
		TSHA6203	I_e	50	65	125	mW/sr
	$I_F = 1 \text{ A}$, $t_p = 100 \mu\text{s}$	TSHA6200	I_e	200	330		mW/sr
		TSHA6201	I_e	260	400		mW/sr
		TSHA6202	I_e	330	460		mW/sr
		TSHA6203	I_e	400	530		mW/sr
Radiant power	$I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$	TSHA6200	ϕ_e		22		mW
		TSHA6201	ϕ_e		23		mW
		TSHA6202	ϕ_e		24		mW
		TSHA6203	ϕ_e		25		mW

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

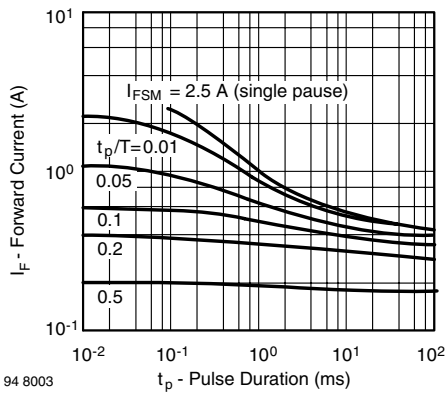


Fig. 3 - Pulse Forward Current vs. Pulse Duration

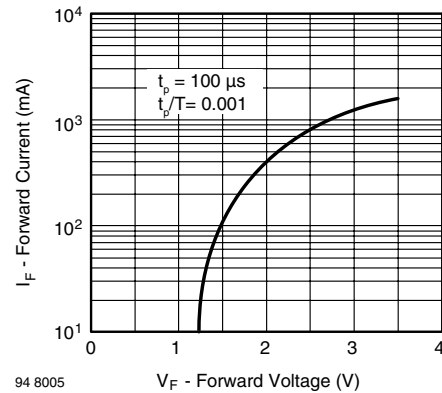


Fig. 4 - Forward Current vs. Forward Voltage

TSHA6200, TSHA6201, TSHA6202, TSHA6203



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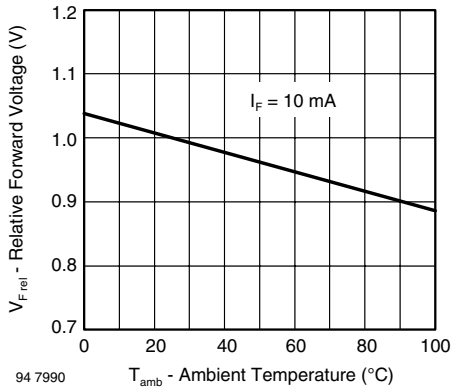


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

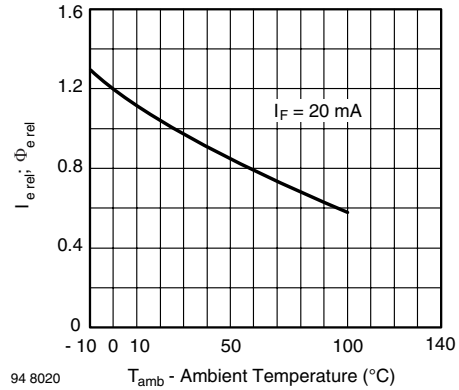


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

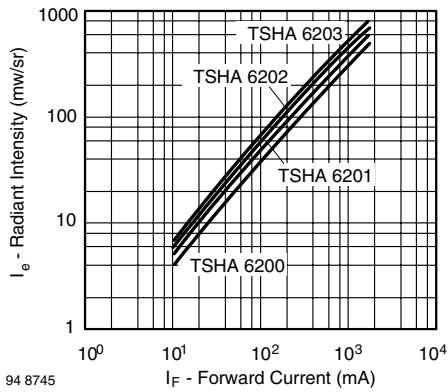


Fig. 6 - Radiant Intensity vs. Forward Current

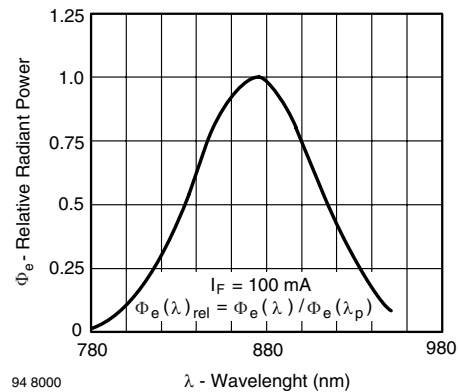


Fig. 9 - Relative Radiant Power vs. Wavelength

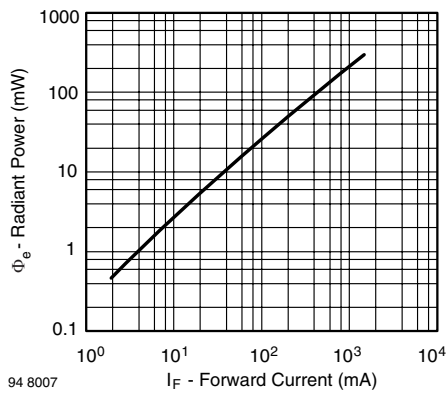


Fig. 7 - Radiant Power vs. Forward Current

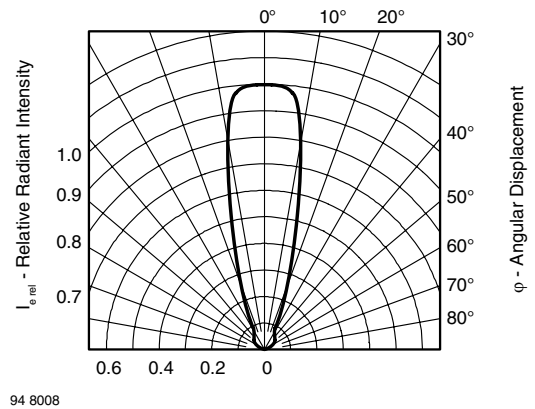


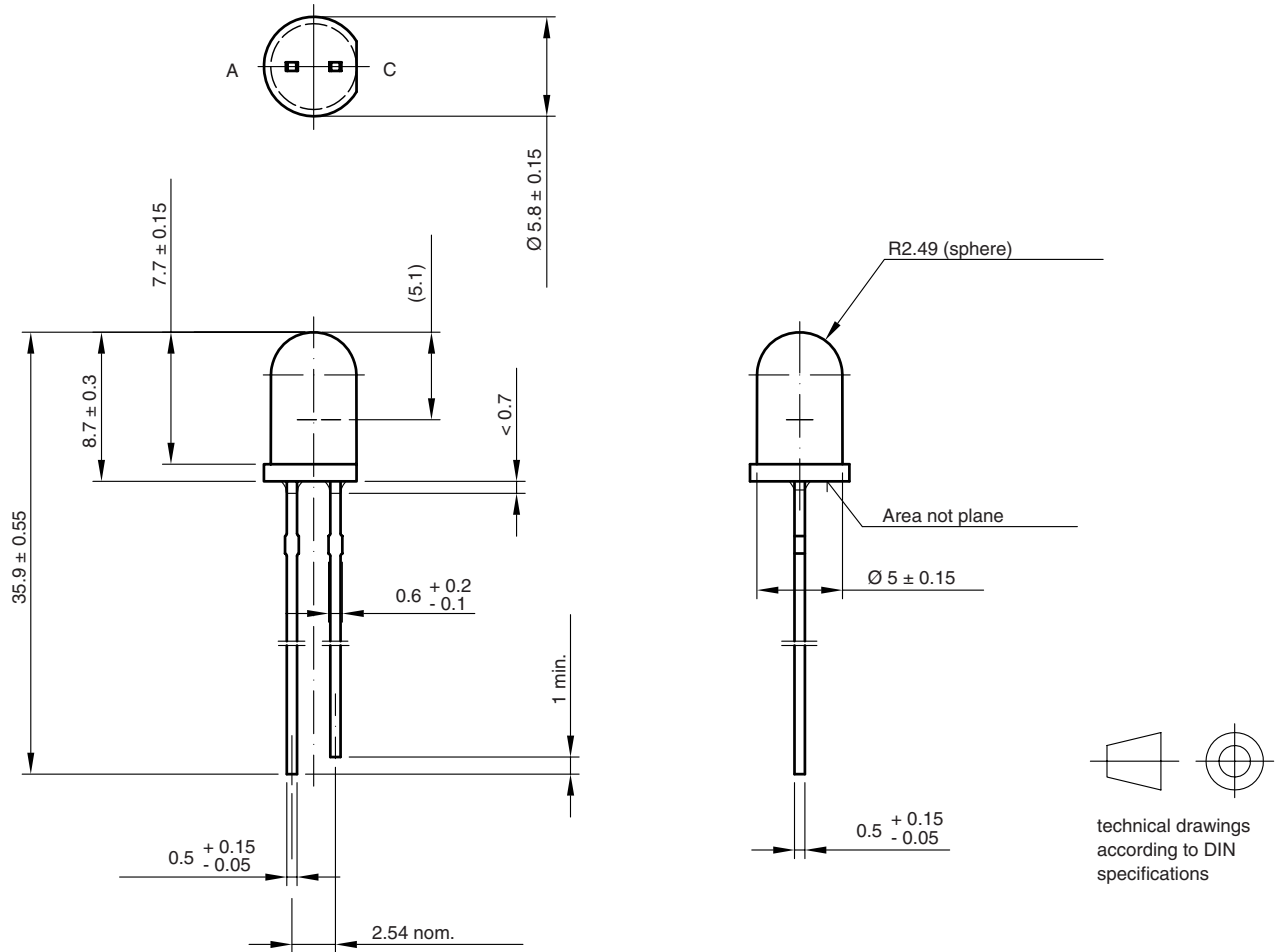
Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



TSHA6200, TSHA6201, TSHA6202, TSHA6203

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PACKAGE DIMENSIONS in millimeters



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96 12125



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